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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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In re Patent Application of:  
CROCE ET AL.

Serial No. 09/839,596

Confirmation No. 1496

Filing Date: April 20, 2001

For: RESURF LDMOS INTEGRATED  
STRUCTURE

Examiner: O. Nadav

Art Unit: 2811

#131 Amelc  
H. Adami  
1/18/03

RESPONSE TO NOTICE OF NON-COMPLIANT AMENDMENT

Director, U.S. Patent and Trademark Office  
Washington, D.C. 20231

Sir:

Responsive to the Notice of Non-Compliant Amendment  
mailed on December 10, 2002, please enter the amendments and  
remarks set out below.

In the Claims:

Please amend Claim 14 as follows:

14. (Amended) A lateral diffused metal oxide  
semiconductor (LDMOS) integrated device comprising:

a semiconductor substrate;

a drain region of a first conductivity type adjacent  
said semiconductor substrate and comprising a superficial  
buffer region being more heavily doped than adjacent portions  
of said drain region;

said superficial buffer region having a dopant  
concentration of about  $5 \times 10^{16}$  to  $5 \times 10^{17}$  atoms  $\text{cm}^{-3}$  and the  
adjacent portions of said drain region having a dopant  
concentration of about  $2.5 \times 10^{15}$  to  $2.5 \times 10^{16}$  atoms  $\text{cm}^{-3}$ ;

a body region surrounded by said superficial buffer  
region and having a second conductivity type; and

a source region in said body region and having the